

UNISONIC TECHNOLOGIES CO., LTD

BT152 **Preliminary SCR**

THYRISTOR

DESCRIPTION

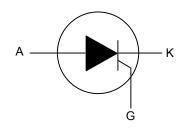
The UTC BT152 is a thyristor, it uses UTC's advanced technology to provide customers with high bidirectional blocking voltage capability and high thermal cycling performance, etc.

The UTC BT152 is suitable for motor control, industrial, static switching, heating and domestic lighting, etc.

FEATURES

- * High bidirectional blocking voltage capability
- * High thermal cycling performance

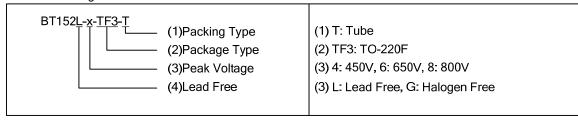
SYMBOL

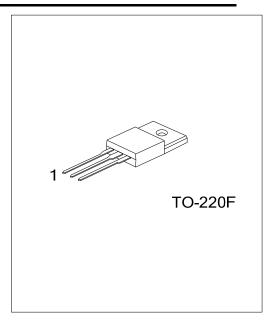


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BT152L-x-TF3-T	BT152G-x-TF3-T	TO-220F	K	Α	G	Tube	

Note: Pin Assignment: K: Cathode G: Gate





■ ABSOLUTE MAXIMUM RATINGS

PARAMETE	SYMBOL	RATINGS	UNIT	
	BT152-4		450	V
Repetitive Peak Off-State Voltages	BT152-6	V_{DRM}, V_{RRM}	650	٧
	BT152-8		800	V
Average On-State Current	Half Sine Wave, T _{MB} ≤103°C	$I_{T(AV)}$	13	Α
RMS On-State Current	All Conduction Angles	$I_{T(RMS)}$	20	Α
Non Repetitive Surge Peak On-State	t=10ms		200	Α
Current (Half Sine Wave; T _J =25°C Prior to Surge)	t=8.3ms	I _{TSM}	220	А
I ² t Value for Fusing	t=10ms	l ² t	200	A^2s
Repetitive Rate of Rise of On-State Current After Triggering	I _{TM} =50A, I _G =0.2A, dI _G /dt=0.2A/μs	dl _⊤ /dt	200	A/µs
Peak Gate Current		I_{GM}	5	Α
Peak Gate Voltage	V_{GM}	5	V	
Peak Reverse Gate Voltage	V_{RGM}	5	V	
Peak Gate Power	P_GM	20	W	
Average Gate Power Dissipation	Over Any 20ms Period	$P_{G(AV)}$	0.5	W
Storage Junction Temperature	T_{STG}	-40~+150	°C	
Operating Junction Temperature	T_J	125	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL RESISTANCES

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	In Free Air	θ_{JA}		60		K/W
Thermal Resistance Junction to Mounting Base		Ө _{ЈМВ}			1.1	K/W

■ STATIC CHARACTERISTICS (T_J=25°C unless otherwise stated)

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate Trigger Current	I _{GT}	V _D =12V, I _T =0.1A		3	32	mΑ
Latching Current	IL	V _D =12V, I _{GT} =0.1A		25	80	mΑ
Holding Current	I _H	V _D =12V, I _{GT} =0.1A		15	60	mΑ
On-State Voltage	V _T	I _T =40A		1.4	1.75	٧
Gate Trigger Voltage	Vot	V _D =12V, I _T =0.1A		0.6	1.5	>
		V _D =V _{DRM(max)} , I _T =0.1A, T _J =125°C	0.25	0.4		٧
Off-State Leakage Current	I_{D}	$V_D = V_{DRM(max)}, V_R = V_{RRM(max)},$		0.2	1.0	mA
	I_R	T _J =125°C		0.2	1.0	mA

■ DYNAMIC CHARACTERISTICS (T_J=25°C unless otherwise stated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Critical Rate of Rise of Off-State Voltage	dV _D /dt	V _{DM} =67%V _{DRM(max)} , T _J =125°C, Exponential Waveform Gate Open Circuit	200	300		V/µs
Gate Controlled Turn-On Time	t _{GT}	V_D = $V_{DRM(max)}$, I_G =0.1A, dI_G/dt =5A/ μ s, I5 $_{TM}$ =40A		2		μs
Circuit Commutated Turn-Off Time	tQ	I_{TM} =50A, V_R =25V, dI_{TM}/dt =30A/ μ s, dV_D/dt =50V/ μ s, R_{GK} =100 Ω		70		μs

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